

DESCRIPTION

MPS4355 is PNP silicon planar epitaxial transistor designed for AF medium power amplifiers.

T0-92



EBC

ABSOLUTE MAXIMUM RATINGS

Collector-Base Voltage	V_{CE0}	60V
Collector-Emitter Voltage	V_{CBO}	60V
Emitter-Base Voltage	V_{EBO}	5V
Collector Current	I_C	1A
Continuous Power Dissipation	P_d	625mW
Operating & Storage Junction Temperature	T_j, T_{stg}	-55 to +150°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	BVCBO	60		V	IC=10μA IE=0
Collector-Emitter Breakdown Voltage	LVCEO	60		V	IC=10mA IB=0*
Emitter-Base Breakdown Voltage	BVEBO	5		V	IE=10μA IC=0
Collector Cutoff Current	ICES		50	nA	VCB=50V VEB=0
D.C. Current Gain	HFE	75			IC=500μA VCE=10V*
		75			IC=100mA VCE=10V*
		100	400		IC=10mA VCE=10V
		75			IC=1mA VCE=10V*
		60			IC=100μA VCE=10V



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Oct-96

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PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Emitter Saturation Voltage	VCE(sat)		0.15	V	IC=150mA IB=15mA*
			0.9	V	IC=500mA IB=50mA*
Base-Emitter Saturation Voltage	VBE(sat)		0.5	V	IC=150mA IB=15mA*
			1.1	V	IC=500mA IB=50mA*
Output Capacitance	Cob		30	pF	VCB=10V f=1MHz
Current Gain-Bandwidth Product	fT	100		MHz	IC=50mA VCE=10V

This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.